

# Dual Switching Diodes

## FEATURE

- Small plastic SMD package.
- For high-speed switching applications.
- Pb-Free Package is available.

## DEVICE MARKING AND ORDERING INFORMATION

| Device     | Marking         | Shipping       |
|------------|-----------------|----------------|
| LBAV70WT1  | A4              | 3000/Tape&Reel |
| LBAV70WT1G | A4<br>(Pb-Free) | 3000/Tape&Reel |

## MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

| Rating                     | Symbol                 | Max | Unit |
|----------------------------|------------------------|-----|------|
| Reverse Voltage            | V <sub>R</sub>         | 70  | Vdc  |
| Forward Current            | I <sub>F</sub>         | 200 | mAdc |
| Peak Forward Surge Current | I <sub>FM(surge)</sub> | 500 | mAdc |

## THERMAL CHARACTERISTICS

| Characteristic                                                                     | Symbol                            | Max         | Unit  |
|------------------------------------------------------------------------------------|-----------------------------------|-------------|-------|
| Total Device Dissipation FR-5 Board <sup>(1)</sup><br>T <sub>A</sub> = 25°C        | P <sub>D</sub>                    | 200         | mW    |
| Derate above 25°C                                                                  |                                   | 1.6         | mW/°C |
| Thermal Resistance, Junction to Ambient                                            | R <sub>θJA</sub>                  | 0.625       | °C/W  |
| Total Device Dissipation<br>Alumina Substrate <sup>(2)</sup> T <sub>A</sub> = 25°C | P <sub>D</sub>                    | 300         | mW    |
| Derate above 25°C                                                                  |                                   | 2.4         | mW/°C |
| Thermal Resistance, Junction to Ambient                                            | R <sub>θJA</sub>                  | 417         | °C/W  |
| Junction and Storage Temperature                                                   | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150 | °C    |

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|----------------|--------|-----|-----|------|
|----------------|--------|-----|-----|------|

## OFF CHARACTERISTICS

|                                                                                                                                        |                 |    |      |      |
|----------------------------------------------------------------------------------------------------------------------------------------|-----------------|----|------|------|
| Reverse Breakdown Voltage<br>(I <sub>BR</sub> = 100 μAdc)                                                                              | V <sub>BR</sub> | 70 | —    | Vdc  |
| Reverse Voltage Leakage Current<br>(V <sub>R</sub> = 70 Vdc)                                                                           | I <sub>R1</sub> | —  | 5.0  | μAdc |
| (V <sub>R</sub> = 50 Vdc)                                                                                                              | I <sub>R2</sub> | —  | 100  | nAdc |
| Diode Capacitance<br>(V <sub>R</sub> = 0, f = 1.0 MHz)                                                                                 | C <sub>D</sub>  | —  | 1.5  | pF   |
| Forward Voltage<br>(I <sub>F</sub> = 1.0 mAdc)                                                                                         | V <sub>F</sub>  | —  | 715  | mVdc |
| (I <sub>F</sub> = 10 mAdc)                                                                                                             |                 | —  | 855  |      |
| (I <sub>F</sub> = 50 mAdc)                                                                                                             |                 | —  | 1000 |      |
| (I <sub>F</sub> = 150 mAdc)                                                                                                            |                 | —  | 1250 |      |
| Reverse Recovery Time<br>(I <sub>F</sub> = I <sub>R</sub> = 10 mAdc, R <sub>L</sub> = 100Ω, I <sub>R(REC)</sub> = 1.0 mAdc) (Figure 1) | t <sub>rr</sub> | —  | 6.0  | ns   |
| Forward Recovery Voltage<br>(I <sub>F</sub> = 10 mAdc, t <sub>r</sub> = 20 ns) (Figure 2)                                              | V <sub>RF</sub> | —  | 1.75 | V    |

1. FR-5 = 1.0 × 0.75 × 0.062 in.

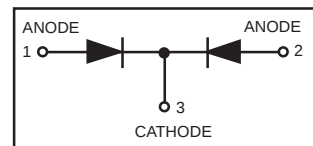
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

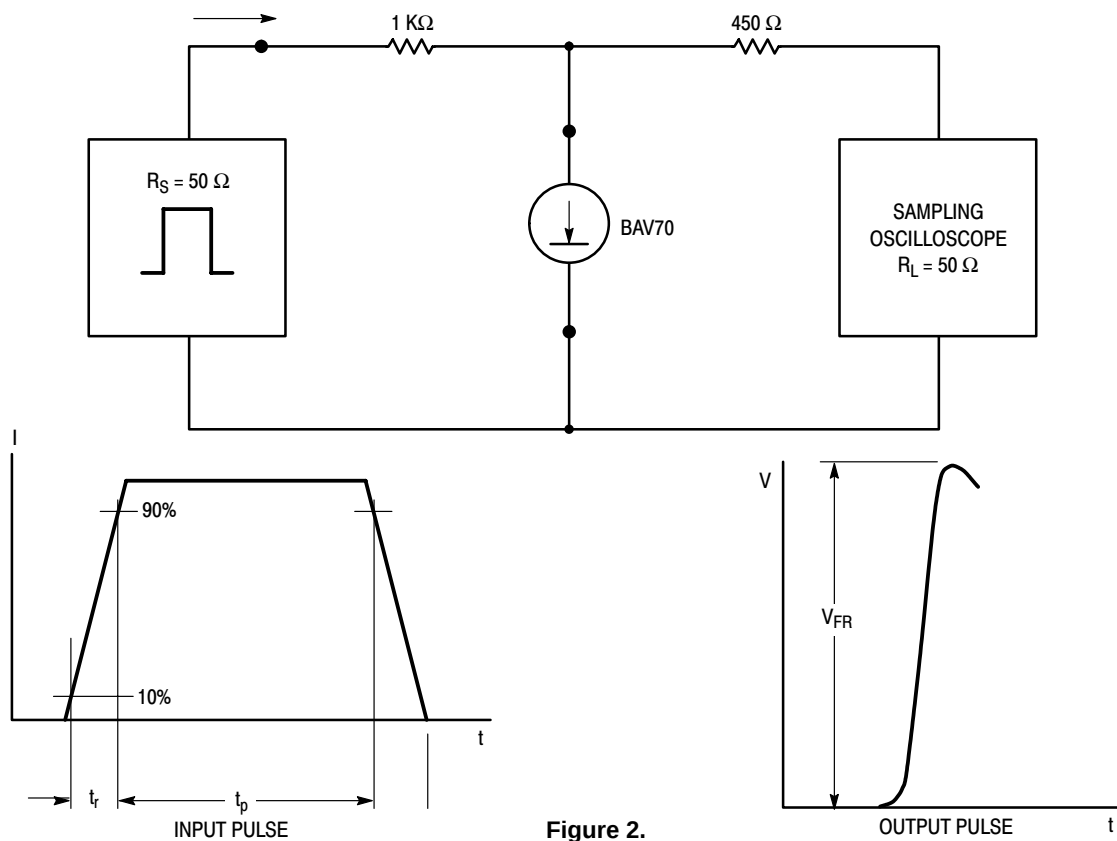
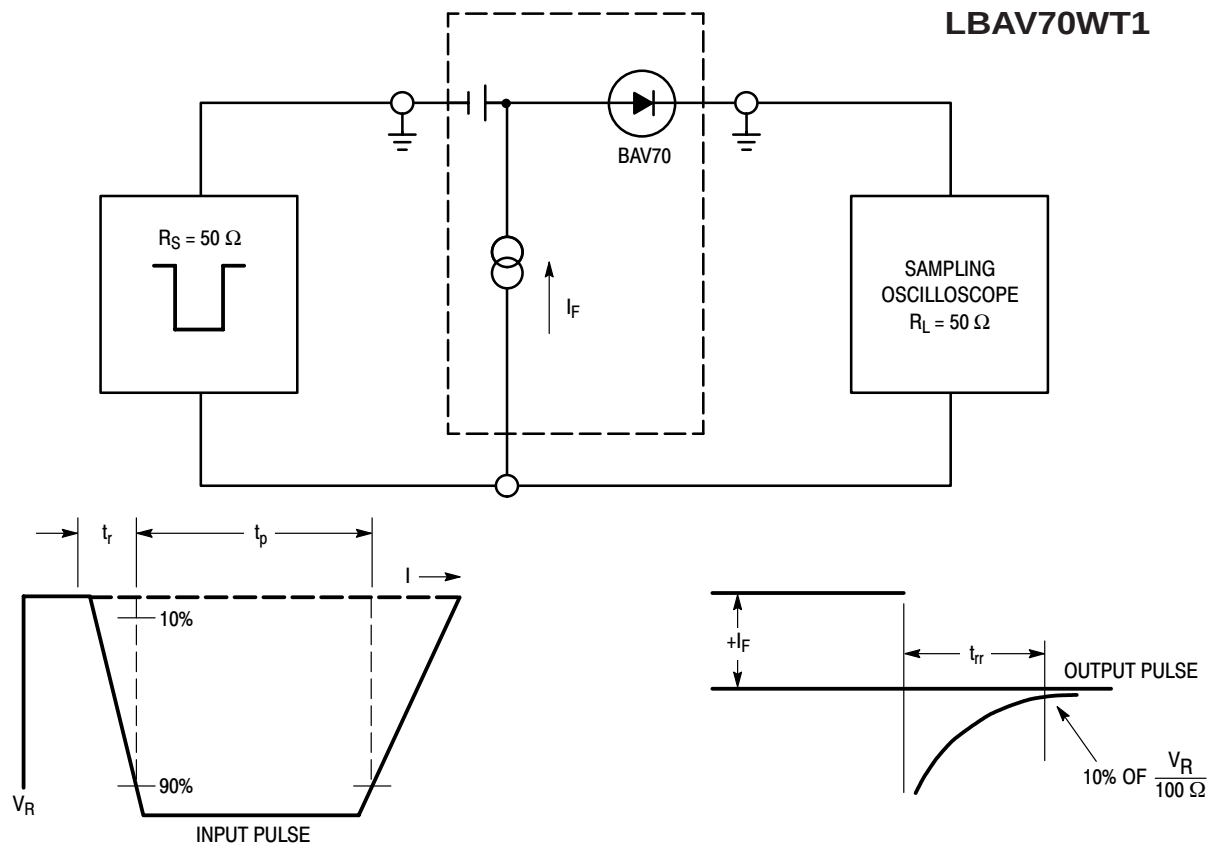
3. For each individual diode while the second diode is unbiased.

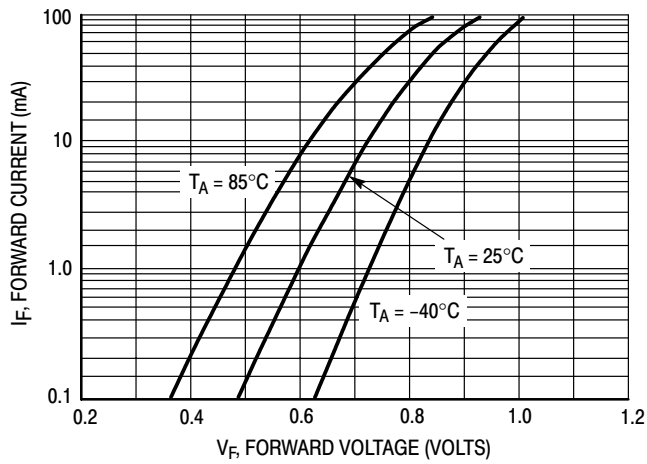
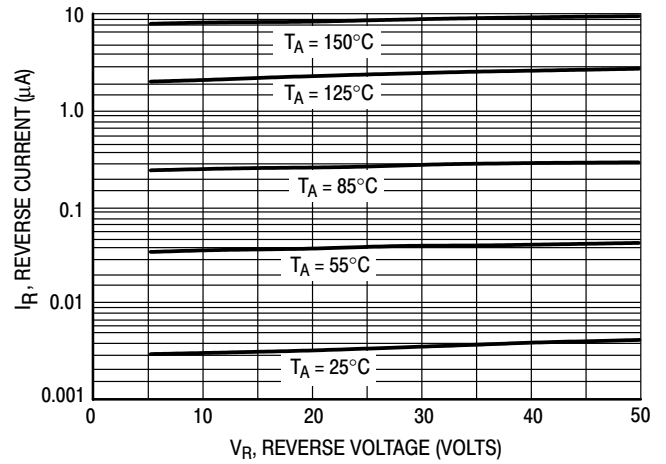
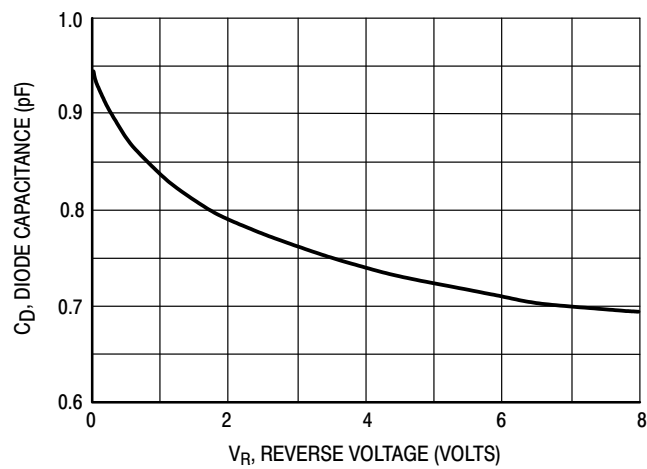
## LBAV70WT1



SOT-323 (SC-70)

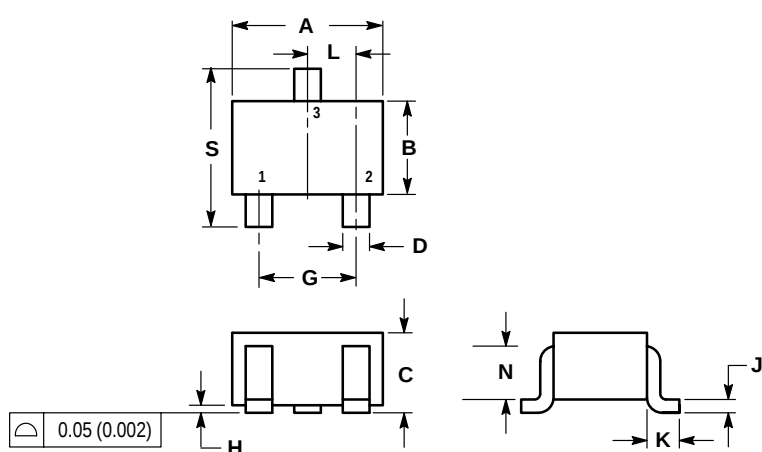




**LBAV70WT1**

**Figure 3. Forward Voltage**

**Figure 4. Leakage Current**

**Figure 5. Capacitance**

**LBAV70WT1**
**SC-70 / SOT-323**
**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



| DIM | INCHES    |       | MILLIMETERS |      |
|-----|-----------|-------|-------------|------|
|     | MIN       | MAX   | MIN         | MAX  |
| A   | 0.071     | 0.087 | 1.80        | 2.20 |
| B   | 0.045     | 0.053 | 1.15        | 1.35 |
| C   | 0.032     | 0.040 | 0.80        | 1.00 |
| D   | 0.012     | 0.016 | 0.30        | 0.40 |
| G   | 0.047     | 0.055 | 1.20        | 1.40 |
| H   | 0.000     | 0.004 | 0.00        | 0.10 |
| J   | 0.004     | 0.010 | 0.10        | 0.25 |
| K   | 0.017 REF |       | 0.425 REF   |      |
| L   | 0.026 BSC |       | 0.650 BSC   |      |
| N   | 0.028 REF |       | 0.700 REF   |      |
| S   | 0.079     | 0.095 | 2.00        | 2.40 |

